ChunZheng

High-end Power Semiconductor Manufacturer

KP300A 2000V-2800V
Phase Control Thyristor

- High power cycling capability
- Low on-state and switching losses
- Designed for traction and industrial applications

Mean on-state current			I_{TAV}	300 A	
Repetitive peak off-state voltage			V_{DRM}	2000 – 2800 V	
Repetitive peak reverse voltage			V_{RRM}		
Turn-off time			t_q	200 µs	
V_{DRM}, V_{RRM}, V	2000	2200	2400	2600	2800
Voltage code	20	22	24	26	28
T_j, °C	-60 – 125				

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Mean on-state current	A	300	T_c=85 °C, Double side cooled 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	471	T_c=85 °C, Double side cooled 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	6.5 7.5	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 50 Hz (t_p=10 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 µs; di_G/dt≥1 A/µs
			6.8 7.8	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 60 Hz (t_p=8.3 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 µs; di_G/dt≥1 A/µs
I^2t	Safety factor	$A^2s\cdot10^3$	211 279	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 50 Hz (t_p=10 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 µs; di_G/dt≥1 A/µs
			193 256	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; 60 Hz (t_p=8.3 ms); single pulse; V_D=V_R=0 V; Gate pulse: I_G=2 A; t_{GP}=50 µs; di_G/dt≥1 A/µs
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	2000–2800	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	2100–2900	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz;single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	0.75·V_{DRM} 0.75·V_{RRM}	T_j=$T_{j\,max}$; Gate open	

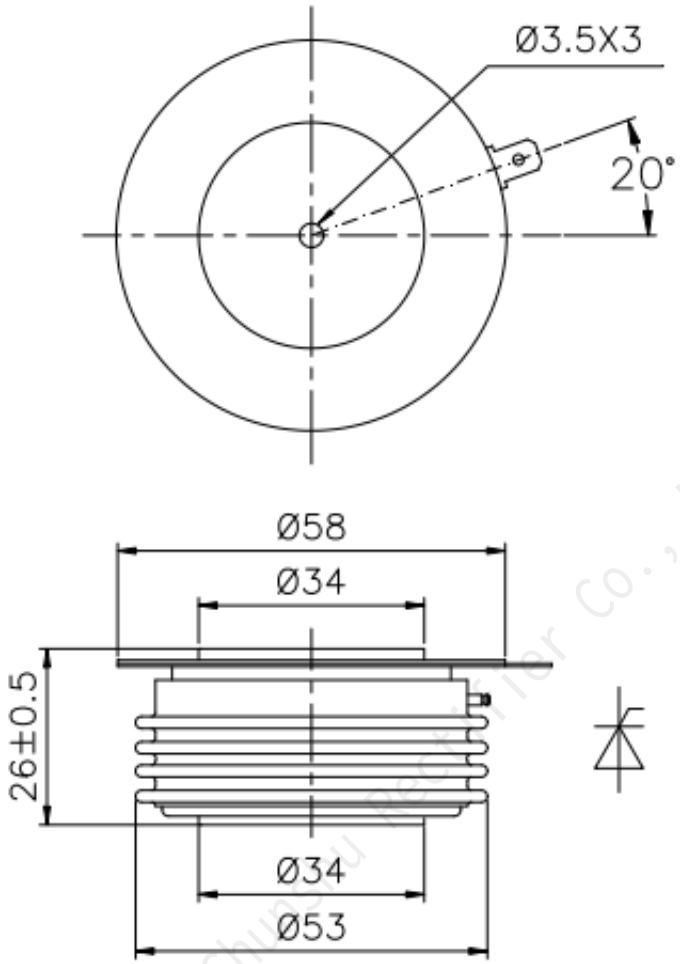
TRIGGERING				
I_{FGM}	Peak forward gate current	A	6	$T_j=T_{j\ max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	3	$T_j=T_{j\ max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/μs	320	$T_j=T_{j\ max}$; $V_D=0.67\cdot V_{DRM}$; $I_{TM}=2\ I_{TAV}$; Gate pulse: $I_G=2$ A; $t_{GP}=50$ μs; $di_G/dt\geq 1$ A/μs
THERMAL				
T_{stg}	Storage temperature	°C	-60 – 125	
T_j	Operating junction temperature	°C	-60 – 125	
MECHANICAL				
F	Mounting force	kN	9.0 – 11.0	
a	Acceleration	m/s^2	50 100	Device unclamped Device clamped

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	2.20	$T_j=25$ °C; $I_{TM}=1005$ A	
$V_{T(TO)}$	On-state threshold voltage, max	V	1.20	$T_j=T_{j\ max}$; $0.5\ \pi\ I_{TAV} < I_T < 1.5\ \pi\ I_{TAV}$	
r_T	On-state slope resistance, max	mΩ	1.510		
I_L	Latching current, max	mA	700	$T_j=25$ °C; $V_D=12$ V; Gate pulse: $I_G=2$ A; $t_{GP}=50$ μs; $di_G/dt\geq 1$ A/μs	
I_H	Holding current, max	mA	300	$T_j=25$ °C; $V_D=12$ V; Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	70	$T_j=T_{j\ max}$; $V_D=V_{DRM}$; $V_R=V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage[1], min	V/μs	1000	$T_j=T_{j\ max}$; $V_D=0.67\cdot V_{DRM}$; Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	2.50 2.00	$T_j=25$ °C $T_j=T_{j\ max}$	$V_D=12$ V; $I_D=3$ A; Direct gate current
I_{GT}	Gate trigger direct current, max	mA	250 200	$T_j=25$ °C $T_j=T_{j\ max}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.25	$T_j=T_{j\ max}$; $V_D=0.67\cdot V_{DRM}$; Direct gate current	
I_{GD}	Gate non-trigger direct current, min	mA	10.00		
SWITCHING					
t_{gd}	Delay time	μs	2.50	$T_j=25$ °C; $V_D=0.4\cdot V_{DRM}$; $I_{TM}=I_{TAV}$; Gate pulse: $I_G=2$ A; $t_{GP}=50$ μs; $di_G/dt\geq 1$ A/μs	
t_q	Turn-off time[2], max	μs	200	$dv_D/dt=50$ V/μs; $T_j=T_{j\ max}$; $I_{TM}=I_{TAV}$; $di_R/dt=-10$ A/μs; $V_R=100$V; $V_D=0.67\cdot V_{DRM}$	

THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.040	Direct current	Double side cooled
R_{thjc-A}			0.088		Anode side cooled
R_{thjc-K}			0.072		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	°C/W	0.008	Direct current	
MECHANICAL					
w	Weight, typ	g	180		
D_s	Surface creepage distance	mm (inch)	19.44 (0.765)		
D_a	Air strike distance	mm (inch)	12.10 (0.476)		

OVERALL DIMENSIONS



KT40

All dimensions in millimeters

